

# Analog Devices Welcomes Hittite Microwave Corporation

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### Typical Applications

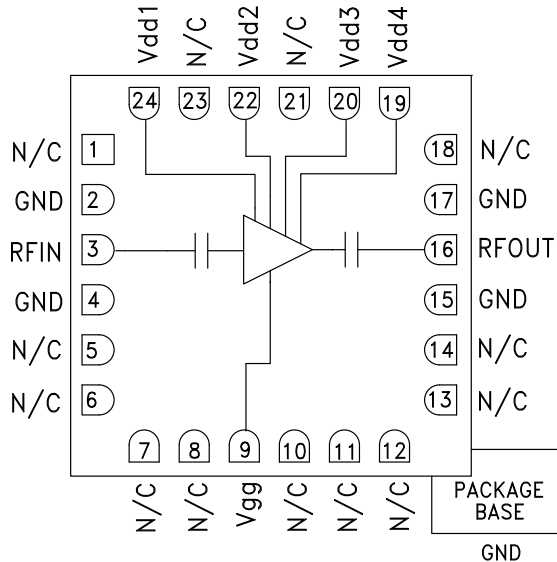
The HMC633LC4 is ideal for:

- Point-to-Point Radios
- Point-to-Multi-Point Radios & VSAT
- LO Driver for Mixers
- Military & Space

### Features

- Gain: 30 dB
- P1dB: +23 dBm
- Saturated Power: +23.8 dBm @ 24% PAE
- Supply Voltage: +5V @180 mA
- 50 Ohm Matched Input/Output
- 24 Lead Ceramic 4x4mm SMT Package: 16mm<sup>2</sup>

### Functional Diagram



### General Description

The HMC633LC4 is a GaAs PHEMT MMIC Driver Amplifier in a leadless 4x4 mm ceramic surface mount package which operates between 5.5 and 17 GHz. The amplifier provides up to 30 dB of gain, +30 dBm Output IP3, and +23 dBm of output power at 1 dB gain compression, while requiring 180 mA from a +5V supply. The HMC633LC4 is an ideal driver amplifier for microwave radio applications from 5.5 to 17 GHz and may be biased at +5V, 130 mA to provide 2 dB lower gain with improved PAE. The amplifier's I/Os are DC blocked and matched to 50 Ohms with no external matching required.

### Electrical Specifications, $T_A = +25^\circ \text{C}$ , $V_{dd_{1-4}} = 5\text{V}$ , $I_{dd} = 180\text{mA}$ [1]

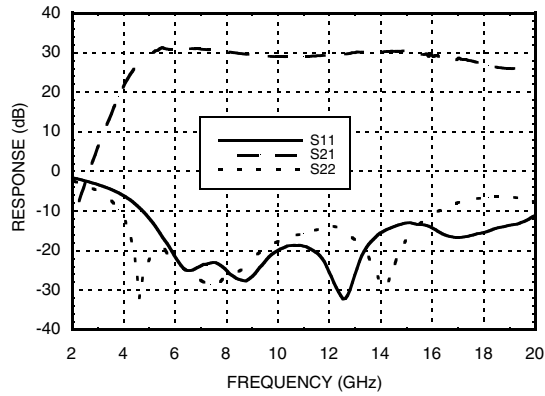
Parameter	Min.	Typ.	Max.	Min.	Typ.	Max.	Units
Frequency Range	5.5 - 9		9 - 17				GHz
Gain	26	30		25	28		dB
Gain Variation Over Temperature		0.030	0.040		0.030	0.040	dB/ °C
Input Return Loss		22			17		dB
Output Return Loss		22			15		dB
Output Power for 1 dB Compression (P1dB)	20	23		18	21		dBm
Saturated Output Power (P <sub>sat</sub> )		23.8			22		dBm
Output Third Order Intercept (IP3)		30			29		dBm
Noise Figure		10			7		dB
Supply Current (I <sub>dd</sub> ) (I <sub>dd</sub> = I <sub>dd1</sub> + I <sub>dd2</sub> + I <sub>dd3</sub> + I <sub>dd4</sub> )		180			180		mA

[1] Adjust V<sub>gg</sub> between -2 to 0V to achieve I<sub>dd</sub> = 180 mA typical.

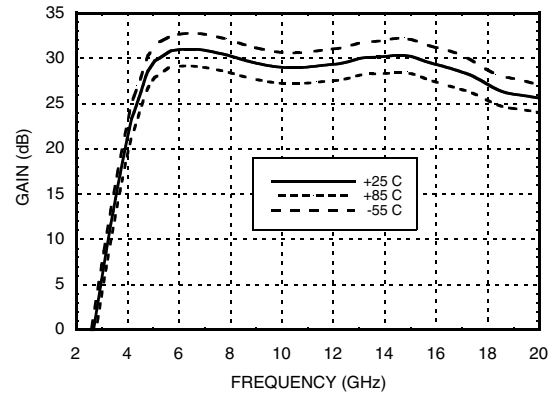


**GaAs PHEMT MMIC DRIVER  
AMPLIFIER, 5.5 - 17 GHz**

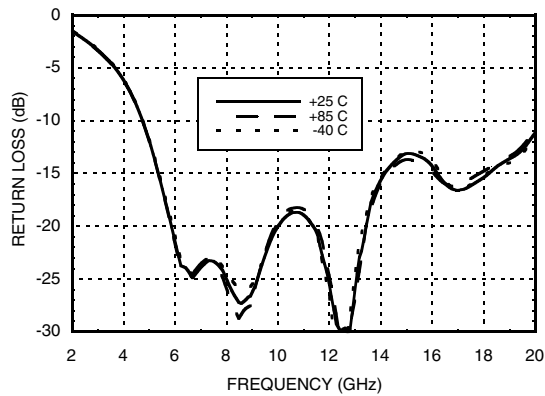
**Broadband Gain & Return Loss**



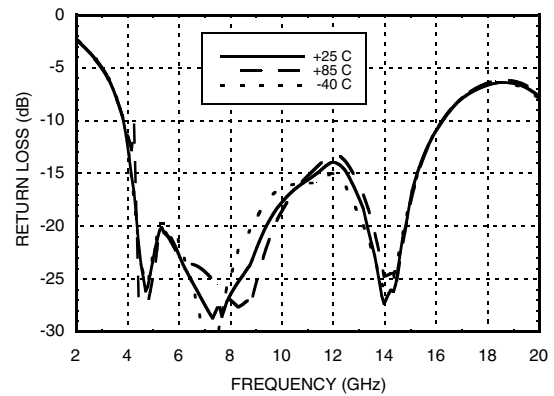
**Gain vs. Temperature**



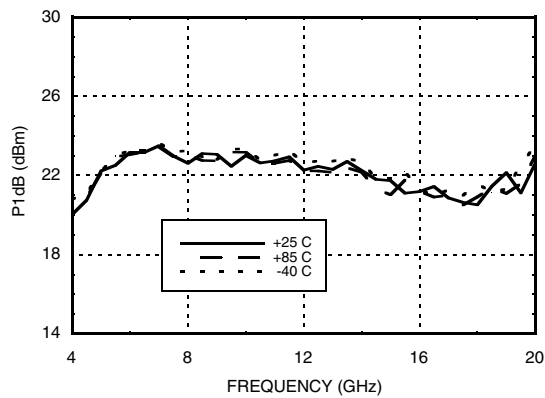
**Input Return Loss vs. Temperature**



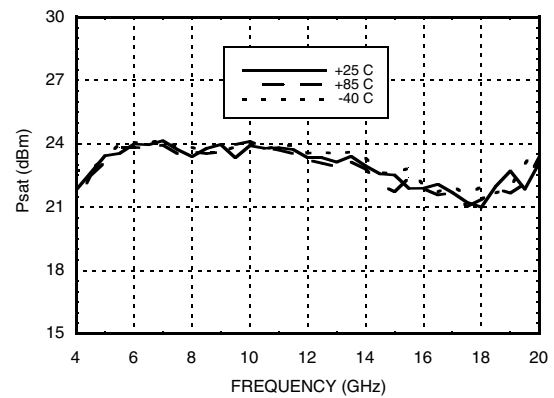
**Output Return Loss vs. Temperature**



**P1dB vs. Temperature**



**Psat vs. Temperature**

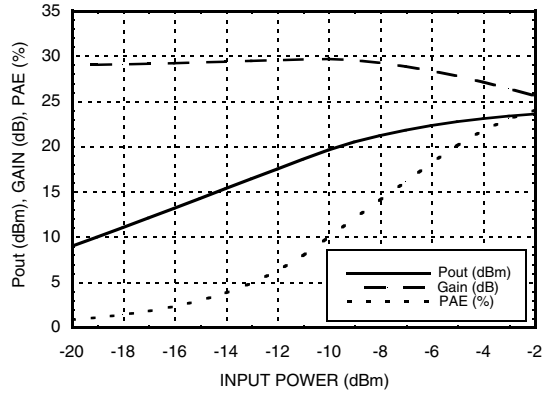




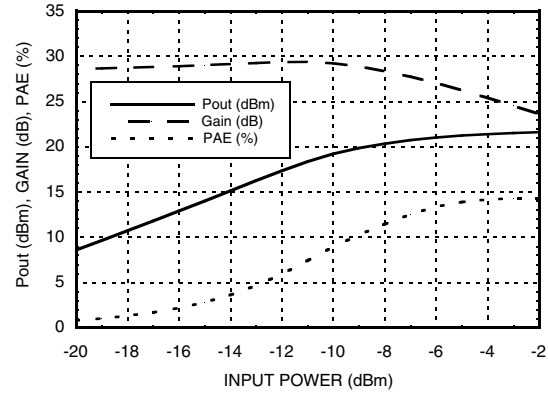
**GaAs PHEMT MMIC DRIVER  
AMPLIFIER, 5.5 - 17 GHz**

DRIVER & GAIN BLOCK AMPLIFIERS - SMT

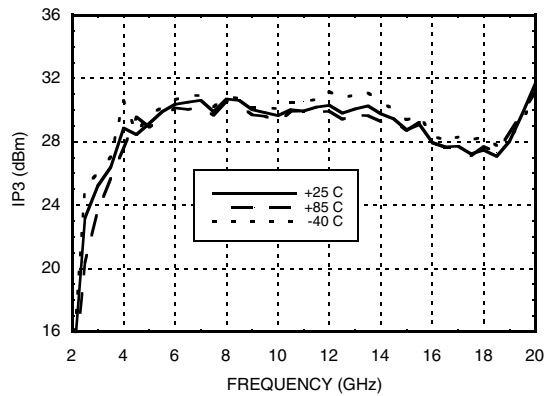
**Power Compression @ 11 GHz**



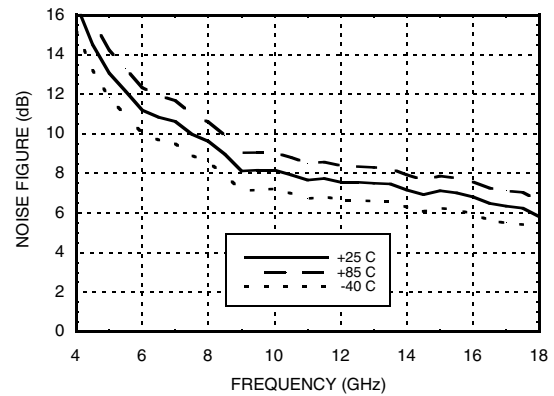
**Power Compression @ 17 GHz**



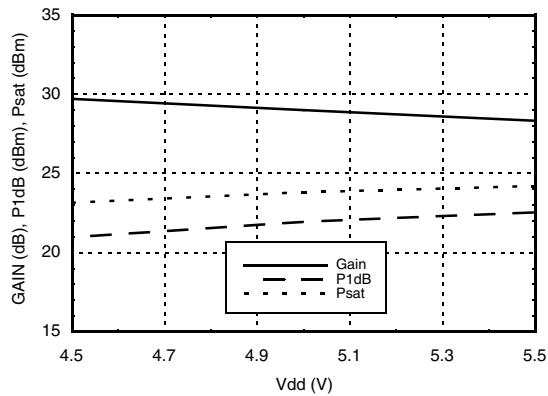
**Output IP3 vs. Temperature**



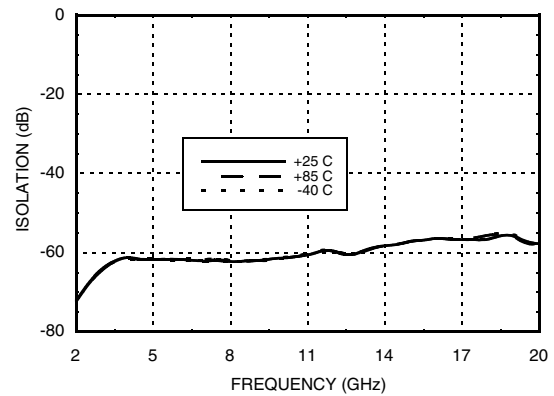
**Noise Figure vs. Temperature**



**Gain & Power vs. Supply Voltage @ 11 GHz**



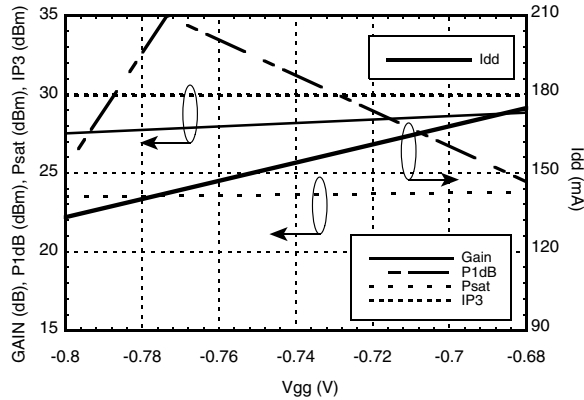
**Reverse Isolation vs. Temperature**





## GaAs PHEMT MMIC DRIVER AMPLIFIER, 5.5 - 17 GHz

### Gain, Power & Output IP3 vs. Gate Voltage @ 11 GHz



### Typical Supply Current vs. Vdd

Vdd (V)	Idd (mA)
4.5	177
5.0	180
5.5	182

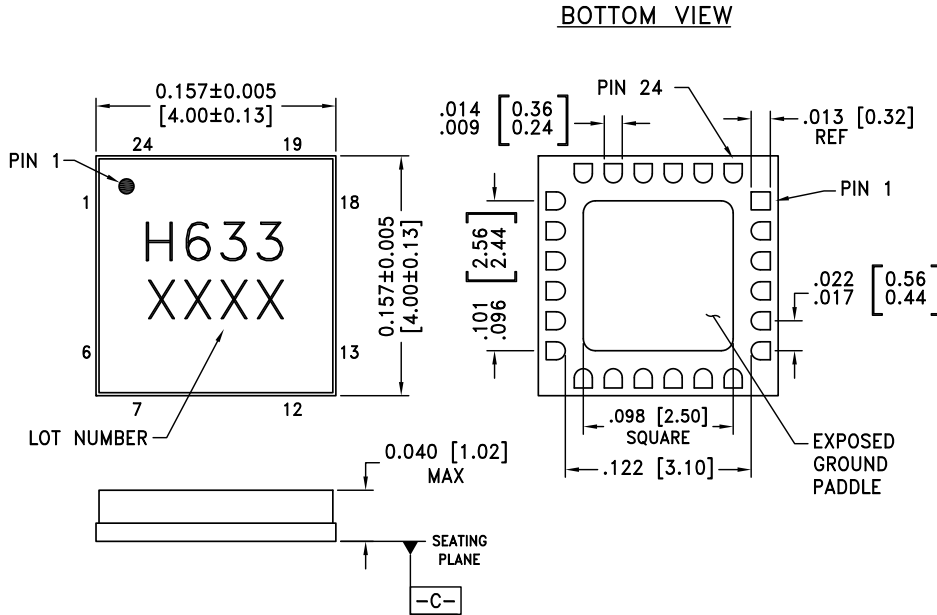
Note: Amplifier will operate over full voltage ranges shown above

### Absolute Maximum Ratings

Drain Bias Voltage (Vdd1, Vdd2, Vdd3, Vdd4)	+5.5V
Gate Bias Voltage (Vgg)	-3 to 0V
RF Input Power (RFIN)(Vdd = +5 Vdc)	+5 dBm
Channel Temperature	175 °C
Continuous P <sub>diss</sub> (T= 85 °C) (derate 11.08 mW/°C above 85 °C)	0.99 W
Thermal Resistance (channel to package bottom)	90.23 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C



ELECTROSTATIC SENSITIVE DEVICE  
OBSERVE HANDLING PRECAUTIONS

**Outline Drawing**

**NOTES:**

1. PACKAGE BODY MATERIAL: ALUMINA
2. LEAD AND GROUND PADDLE PLATING: 30-80 MICROINCHES GOLD OVER 50 MICROINCHES MINIMUM NICKEL.
3. DIMENSIONS ARE IN INCHES [MILLIMETERS].
4. LEAD SPACING TOLERANCE IS NON-CUMULATIVE.
5. PACKAGE WARP SHALL NOT EXCEED 0.05mm DATUM -C-
6. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.


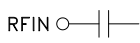
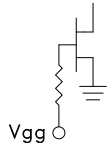
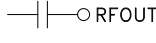

**Package Information**

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking <sup>[2]</sup>
HMC633LC4	Alumina, White	Gold over Nickel	MSL3 <sup>[1]</sup>	H633 XXXX

[1] Max peak reflow temperature of 260 °C

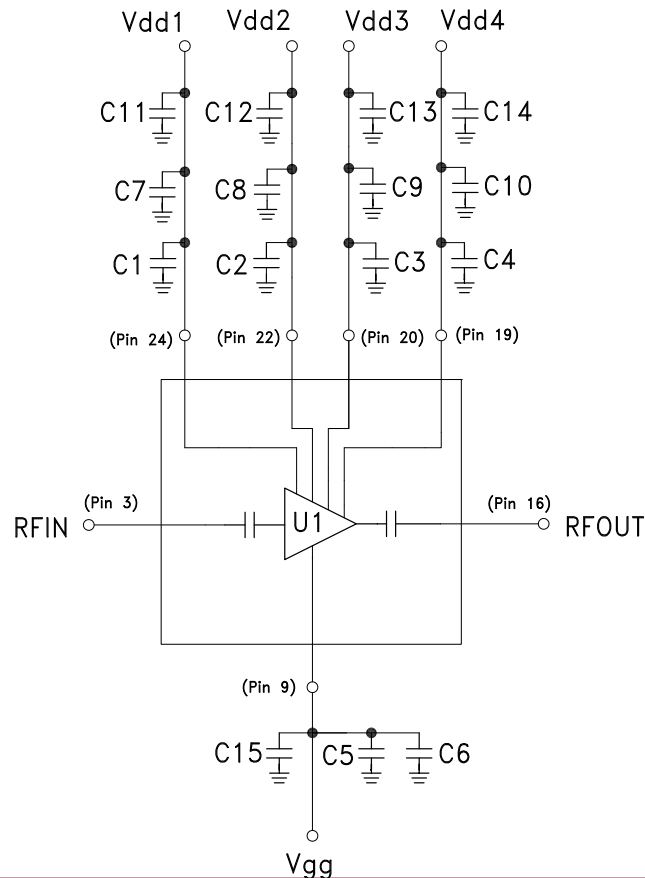
[2] 4-Digit lot number XXXX

**Pin Descriptions**

Pin Number	Function	Description	Interface Schematic
1, 5 - 8, 11 - 14, 18, 21, 23	N/C	No connection. These pins may be connected to DC/RF ground. Performance will not be affected.	
2, 4, 15, 17	GND	Package Bottom must be connected to RF/DC ground.	
3	RFIN	This pin is AC coupled and matched to 50 Ohms.	
9	Vgg	Gate control for amplifier, please follow "MMIC Amplifier Biasing Procedure" Application Note: See application circuit for required external components.	
16	RFOUT	This pin is AC coupled and matched to 50 Ohms.	
24, 22, 20, 19	Vdd1, Vdd2, Vdd3, Vdd4	Power Supply Voltage for the amplifier. See application circuit for required external components.	

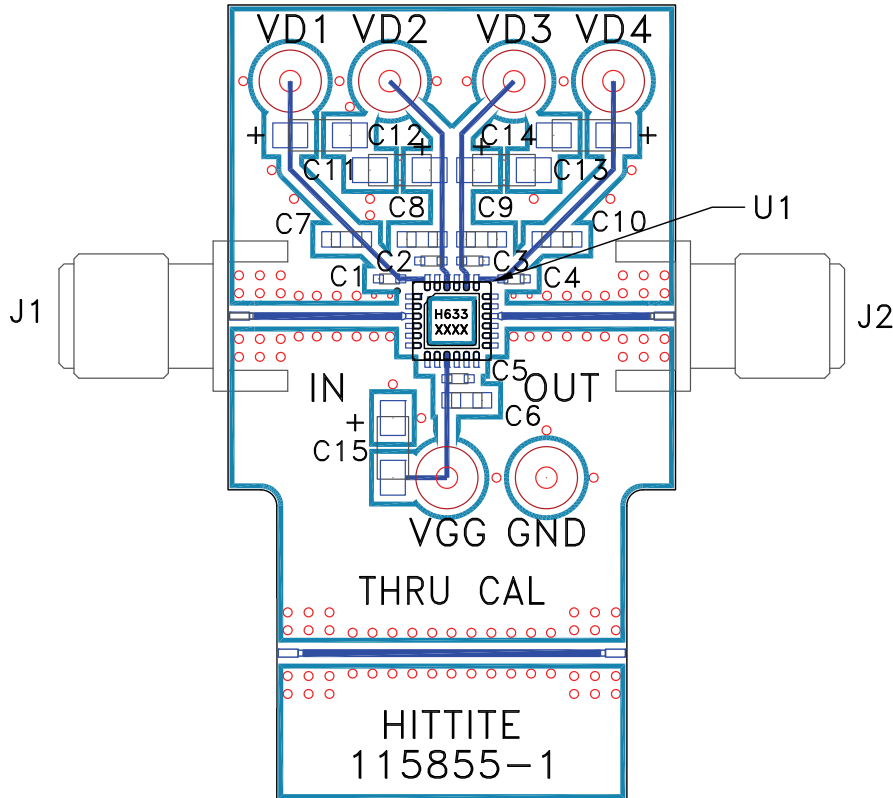
**Application Circuit**

Component	Value
C1 - C5	100 pF
C6 - C10	1000 pF
C11 - C15	2.2 $\mu$ F





### Evaluation PCB



### List of Materials for Evaluation PCB 115857 [1]

Item	Description
J1 - J2	2.92 mm PC Mount K-Connector
VD1 - VD4	DC Pin
C1 - C5	100 pF Capacitor, 0402 Pkg.
C6 - C10	1000 pF Capacitor, 0603 Pkg.
C11 - C15	2.2 μF Capacitor, Tantalum
U1	HMC633LC4 Driver Amplifier
PCB [2]	115855 Evaluation PCB

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.



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